NSN 5961-01-330-3638

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-330-3638 **Inclosure Material:** Ceramic **Overall Length:** 0.350 inches **Overall Height:** 0.090 inches Overall Width: 0.350 inches **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 40.0 collector to base voltage, dc all transistor and 40.0 collector to emitter voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 10.00 milliamperes source cutoff current all transistor and 50.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 1.2 watts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: pnp **Test Data Document:** 07187-8256252 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 20 printed circuit Shelf Life: N/a **Unit Of Measure: Demilitarization:** No